

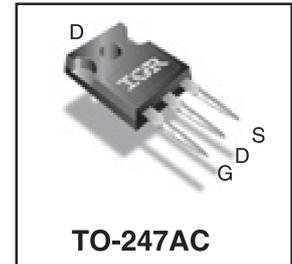
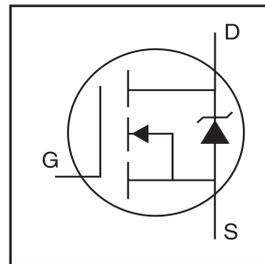
**PDP SWITCH**

**IRFP4227PbF**

**Features**

- Advanced Process Technology
- Key Parameters Optimized for PDP Sustain, Energy Recovery and Pass Switch Applications
- Low  $E_{PULSE}$  Rating to Reduce Power Dissipation in PDP Sustain, Energy Recovery and Pass Switch Applications
- Low  $Q_G$  for Fast Response
- High Repetitive Peak Current Capability for Reliable Operation
- Short Fall & Rise Times for Fast Switching
- 175°C Operating Junction Temperature for Improved Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability

Key Parameters		
$V_{DS\ max}$	200	V
$V_{DS\ (Avalanche)\ typ.}$	240	V
$R_{DS(ON)\ typ.\ @\ 10V}$	21	mΩ
$I_{RP\ max\ @\ T_C = 100^\circ C}$	130	A
$T_J\ max$	175	°C



G	D	S
Gate	Drain	Source

**Description**

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low  $E_{PULSE}$  rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{GS}$	Gate-to-Source Voltage	±30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	65	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	46	
$I_{DM}$	Pulsed Drain Current ①	260	
$I_{RP} @ T_C = 100^\circ C$	Repetitive Peak Current ⑤	130	
$P_D @ T_C = 25^\circ C$	Power Dissipation	330	W
$P_D @ T_C = 100^\circ C$	Power Dissipation	190	
	Linear Derating Factor	2.2	W/°C
$T_J$	Operating Junction and Storage Temperature Range	-40 to + 175	°C
$T_{STG}$			
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ④	—	62	

Notes ① through ⑥ are on page 8